WHAT IS CLAIMED IS:

1. A package structure, comprising:

an insulation layer;

an electronic component embedded within the insulation layer, and comprising plural conducting terminals; and

a lead frame unit embedded within the insulation layer, comprising:

a lead frame; and

a metallization layer having a thickness more than 10 μm disposed on at least a part of the lead frame and electrically connected with at least one of the plural conducting terminals of the electronic component.

2. The package structure according to claim 1, wherein the metallization layer is disposed on at least a part of a top surface of the lead frame.

3. The package structure according to claim 1, wherein the metallization layer is disposed on at least a part of a bottom surface of the lead frame.

4. The package structure according to claim 1, wherein the metallization layer is disposed on at least a part of plural sidewalls of the lead frame.

5. The package structure according to claim 1, wherein the metallization layer is disposed on a whole outer surface of the lead frame.

6. The package structure according to claim 1, wherein the thickness of the metallization layer is smaller than 30 μm.

7. The package structure according to claim 1, wherein the metallization layer is disposed on at least a part of the lead frame by electroplating.

8. The package structure according to claim 1, wherein the metallization layer is made of copper, tin, silver, nickel, chromium or a combination thereof.

9. The package structure according to claim 1, further comprising two redistribution layers, wherein one part of the redistribution layer is disposed on a top surface or a bottom surface of the insulation layer, and the other part of the redistribution layer is located in the insulation layer and connected with at least one of the plural conducting terminals and at least a part of the lead frame

unit.

10. The package structure according to claim 1, wherein the electronic component is disposed on a top surface of the lead frame unit, a bottom surface of the lead frame unit is exposed to the insulation layer, the package structure further comprises at least one conducting wire, and the conducting wire is electrically connected with at least one of the plural conducting terminals and the lead frame unit.

11. A method of manufacturing a package structure, comprising steps of:

(a) providing an electronic component comprising plural conducting terminals;

(b) providing a lead frame unit comprising a lead frame and a metallization layer, the metallization layer being disposed on at least a part of the lead frame and having a thickness more than 10 μm;

(c) performing an interconnection process to electrically connect the lead frame unit and at least one of the plural conducting terminals; and

(d) embedding the electronic component and the lead frame unit within an insulation layer.

12. The method according to claim 11, wherein in the step (b), the metallization layer is disposed on at least a part of a top surface of the lead frame.

13. The method according to claim 11, wherein in the step (b), the metallization layer is disposed on at least a part of a bottom surface of the lead frame.

14. The method according to claim 11, wherein in the step (b), the metallization layer is disposed on at least a part of plural sidewalls of the lead frame.

15. The method according to claim 11, wherein in the step (c), a wire bonding process is performed to form a conducting wire electrically connected between the lead frame unit and at least one of the plural conducting terminals.

16. The method according to claim 11, wherein the thickness of the metallization layer is smaller than 30 μm.

17. The method according to claim 11, wherein in the step (b), the metallization layer is disposed on at least a part of the lead frame by electroplating.

18. The method according to claim 11, wherein the metallization layer is made of copper, tin, silver, nickel, chromium or a combination thereof.

19. The method according to claim 11, wherein in the step (c), at least one redistribution layer is formed on a top surface or a bottom surface of the insulation layer, and electrically connected with the metallization layer of the lead frame unit and at least one of the plural conducting terminals.

20. The method according to claim 11, wherein the electronic component is disposed on a top surface of the lead frame unit, and a bottom surface of the lead frame unit is exposed to the insulation layer.